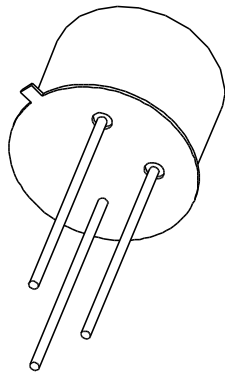


DATA SHEET



BFT45

PNP high-voltage transistor

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Apr 18

PNP high-voltage transistor

BFT45

FEATURES

- Low current (max. 500 mA)
- High voltage (max. 250 V).

APPLICATIONS

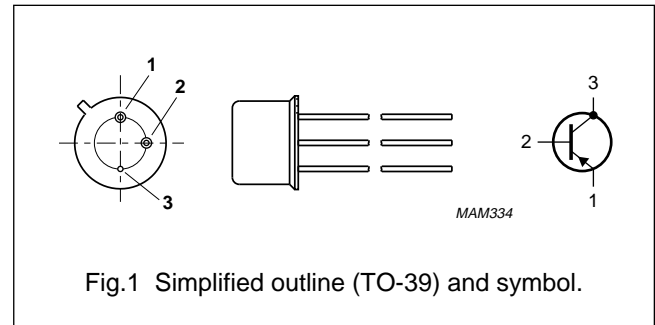
- High voltage switching and amplification
- Industrial and telephone applications.

DESCRIPTION

PNP high-voltage transistor in a TO-39 metal package.

PINNING

| PIN | DESCRIPTION |
|-----|------------------------------|
| 1 | emitter |
| 2 | base |
| 3 | collector, connected to case |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|---------------------------|--|------|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | – | – | –250 | V |
| V_{CEO} | collector-emitter voltage | open base | – | – | –250 | V |
| I_{CM} | peak collector current | | – | – | –1 | A |
| P_{tot} | total power dissipation | $T_{case} \leq 50\text{ }^{\circ}\text{C}$ | – | – | 5 | W |
| h_{FE} | DC current gain | $I_C = -10\text{ mA}; V_{CE} = -10\text{ V}$ | 50 | – | 150 | |
| C_c | collector capacitance | $I_E = i_e = 0; V_{CE} = -20\text{ V}; f = 1\text{ MHz}$ | – | – | 15 | pF |
| f_T | transition frequency | $I_C = -15\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$ | – | 70 | – | MHz |

PNP high-voltage transistor

BFT45

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|-------------------------------|--|------|------|------------------|
| V_{CBO} | collector-base voltage | open emitter | – | –250 | V |
| V_{CEO} | collector-emitter voltage | open base | – | –250 | V |
| V_{EBO} | emitter-base voltage | open collector | – | –5 | V |
| I_C | collector current (DC) | | – | –500 | mA |
| I_{CM} | peak collector current | | – | –1 | A |
| I_{BM} | peak base current | | – | –200 | mA |
| P_{tot} | total power dissipation | $T_{case} \leq 50\text{ }^\circ\text{C}$ | – | 5 | W |
| T_{stg} | storage temperature | | –65 | +150 | $^\circ\text{C}$ |
| T_j | junction temperature | | – | 200 | $^\circ\text{C}$ |
| T_{amb} | operating ambient temperature | | –65 | +150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------|---|-------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | in free air | 200 | K/W |
| $R_{th\ j-c}$ | thermal resistance from junction to case | | 30 | K/W |

CHARACTERISTICS $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------|--------------------------------------|--|------|------|------|---------------|
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = -200\text{ V}$ | – | – | –5 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = -3\text{ V}$ | – | – | –5 | μA |
| h_{FE} | DC current gain | $I_C = -1\text{ mA}; V_{CE} = -10\text{ V}$ | 30 | – | – | |
| | | $I_C = -10\text{ mA}; V_{CE} = -10\text{ V}$ | 50 | – | 150 | |
| | | $I_C = -100\text{ mA}; V_{CE} = -10\text{ V};$ note 1 | 50 | – | – | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = -10\text{ mA}; I_B = -1\text{ mA}$ | – | – | –0.5 | V |
| | | $I_C = -100\text{ mA}; I_B = -10\text{ mA}$ | – | – | –1.4 | V |
| | | $I_C = -500\text{ mA}; I_B = -100\text{ mA};$ note 1 | – | – | –3 | V |
| V_{BEsat} | base-emitter saturation voltage | $I_C = -10\text{ mA}; I_B = -1\text{ mA}$ | – | – | –0.5 | V |
| | | $I_C = -100\text{ mA}; I_B = -10\text{ mA}$ | – | – | –0.9 | V |
| | | $I_C = -500\text{ mA}; I_B = -100\text{ mA};$ note 1 | – | – | –1.2 | V |
| C_c | collector capacitance | $I_E = i_e = 0; V_{CB} = -20\text{ V}; f = 1\text{ MHz}$ | – | – | 15 | pF |
| f_T | transition frequency | $I_C = -15\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$ | – | 70 | – | MHz |

Note1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

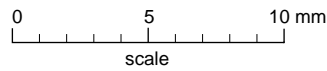
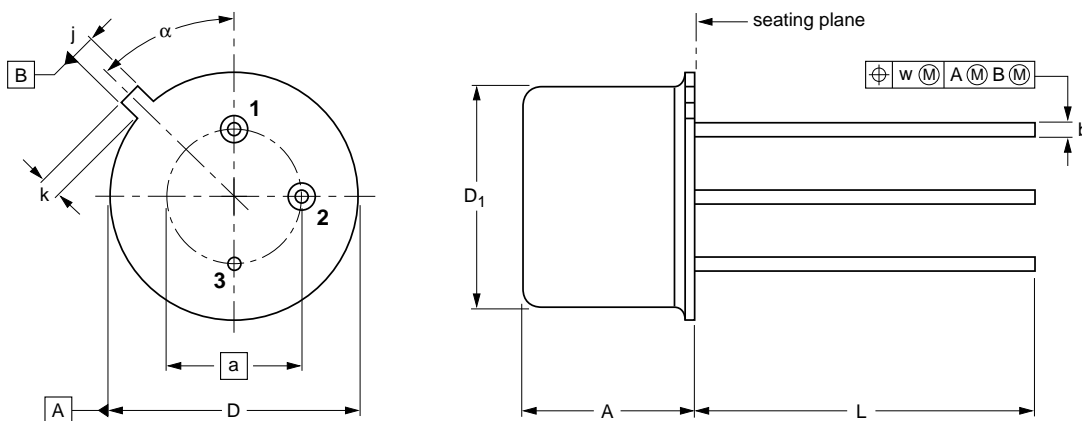
PNP high-voltage transistor

BFT45

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

| UNIT | A | a | b | D | D ₁ | j | k | L | w | α |
|------|------|------|------|------|----------------|------|------|-----|-----|---|
| mm | 6.60 | 0.48 | 9.39 | 8.33 | 0.85 | 0.95 | 14.2 | 0.2 | 45° | |
| | 6.35 | 5.08 | 0.41 | 9.08 | 8.18 | 0.75 | 12.7 | | | |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT5/11 | | TO-39 | | | | 97-04-11 |

PNP high-voltage transistor

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DEFINITIONS

| | |
|---|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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NOTES

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